
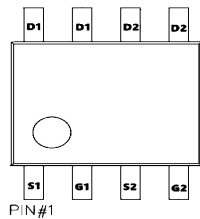




TM10V03S

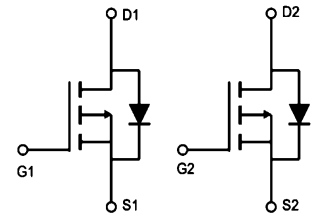
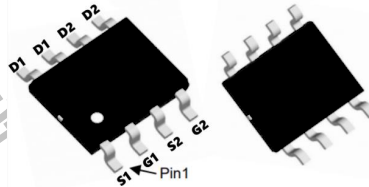
P+P-Channel Enhancement Mode Mosfet

| | |
|--|--|
| <p>General Description</p> <ul style="list-style-type: none"> • Low $R_{DS(ON)}$ • RoHS and Halogen-Free Compliant <p>Applications</p> <ul style="list-style-type: none"> • Load switch • PWM | <p>General Features</p> <p>$V_{DS} = -30V$ $I_D = -9.8A$</p> <p>$R_{DS(ON)} = 12m\Omega$(typ.)@ $V_{GS} = -10V$</p> <p>100% UIS Tested 100% R_g Tested</p>  |
|--|--|



Marking:4805

S:SOP-8L



Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

| Symbol | Parameter | Rating | Units |
|---------------------------|--|------------|------------|
| V_{DS} | Drain-Source Voltage | -30 | V |
| V_{GS} | Gate-Source Voltage | ± 20 | V |
| $I_D @ T_C = 25^\circ C$ | Continuous Drain Current, $-V_{GS} @ -10V^1$ | -9.8 | A |
| $I_D @ T_C = 100^\circ C$ | Continuous Drain Current, $-V_{GS} @ -10V^1$ | -6.2 | A |
| I_{DM} | Pulsed Drain Current ² | -40 | A |
| $P_D @ T_A = 25^\circ C$ | Total Power Dissipation ³ | 3.7 | W |
| T_{STG} | Storage Temperature Range | -55 to 175 | $^\circ C$ |
| T_J | Operating Junction Temperature Range | -55 to 175 | $^\circ C$ |

Thermal Data

| Symbol | Parameter | Typ. | Max. | Unit |
|-----------------|--|------|------|--------------|
| $R_{\theta JA}$ | Thermal Resistance Junction-Ambient ¹ | --- | 85 | $^\circ C/W$ |
| $R_{\theta JC}$ | Thermal Resistance Junction-Case ¹ | --- | 36 | $^\circ C/W$ |



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Electrical Characteristics (T_J=25°C unless otherwise specified)

| Symbol | Parameter | Test Condition | Min. | Typ. | Max. | Units |
|---|--|---|------|------|------|-------|
| Off Characteristic | | | | | | |
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D = -250μA | -30 | - | - | V |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = -30V, V _{GS} =0V, | - | - | -1 | μA |
| I _{GSS} | Gate to Body Leakage Current | V _{DS} =0V, V _{GS} = ±20V | - | - | ±100 | nA |
| On Characteristics | | | | | | |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D = -250μA | -1.0 | -1.5 | -2.0 | V |
| R _{DS(on)} | Static Drain-Source on-Resistance Note3 | V _{GS} = -10V, I _D = -10A | - | 12 | 21 | mΩ |
| | | V _{GS} = -4.5V, I _D = -5A | - | 22 | 27 | |
| Dynamic Characteristics | | | | | | |
| C _{iss} | Input Capacitance | V _{DS} = -15V, V _{GS} =0V, f=1.0MHz | - | 1390 | - | pF |
| C _{oss} | Output Capacitance | | - | 183 | - | pF |
| C _{rss} | Reverse Transfer Capacitance | | - | 156 | - | pF |
| Q _g | Total Gate Charge | V _{DS} = -15V, I _D = -5A, V _{GS} = -10V | - | 22 | - | nC |
| Q _{gs} | Gate-Source Charge | | - | 1.0 | - | nC |
| Q _{gd} | Gate-Drain("Miller") Charge | | - | 1.8 | - | nC |
| Switching Characteristics | | | | | | |
| t _{d(on)} | Turn-on Delay Time | V _{DD} = -15V, I _D = -10A, V _{GS} =-10V, R _{GEN} =2.5Ω | - | 9 | - | ns |
| t _r | Turn-on Rise Time | | - | 13 | - | ns |
| t _{d(off)} | Turn-off Delay Time | | - | 48 | - | ns |
| t _f | Turn-off Fall Time | | - | 20 | - | ns |
| Drain-Source Diode Characteristics and Maximum Ratings | | | | | | |
| I _S | Maximum Continuous Drain to Source Diode Forward Current | | - | - | -9.8 | A |
| I _{SM} | Maximum Pulsed Drain to Source Diode Forward Current | | - | - | -40 | A |
| V _{SD} | Drain to Source Diode Forward Voltage | V _{GS} =0V, I _S = -15A | - | -0.8 | -1.2 | V |
| t _{rr} | Reverse Recovery Time | T _J =25°C, | - | 64 | - | ns |
| Q _{rr} | Reverse Recovery Charge | V _{DD} = -24V, I _F =-2.8A, dI/dt=-100A/μs | - | 25 | - | nC |

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: T_J=25°C, V_{GS}=10V, R_G=25Ω, L=0.5mH, I_{AS}=-12.7A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

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Typical Performance Characteristics

Figure 1: Output Characteristics

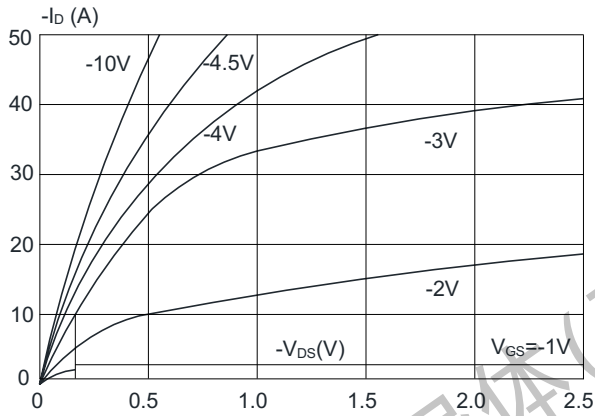


Figure 2: Typical Transfer Characteristics

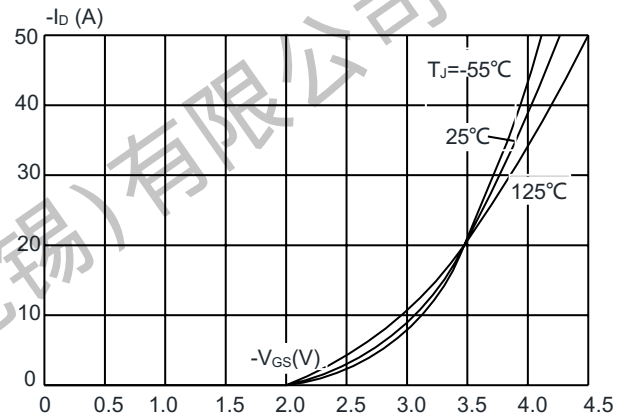


Figure 3: On-resistance vs. Drain Current

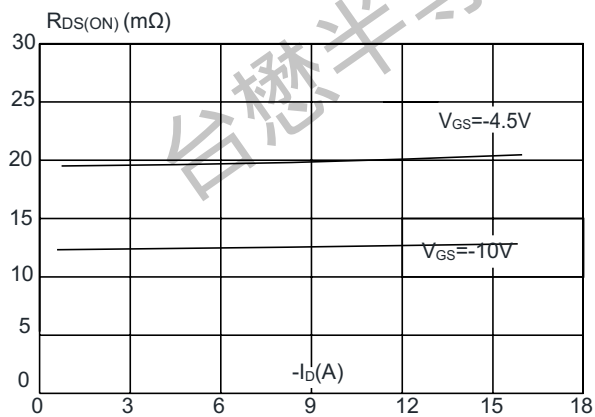


Figure 4: Body Diode Characteristics

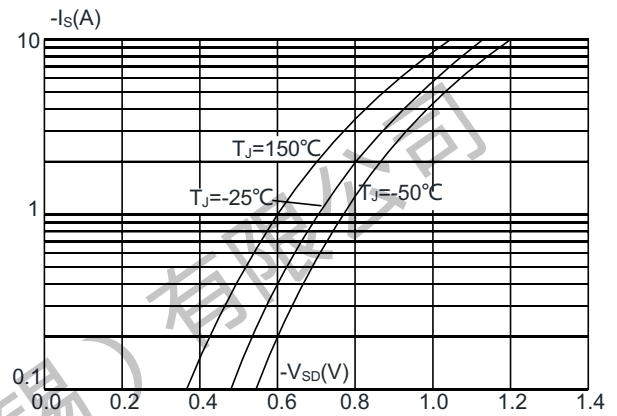


Figure 5: Gate Charge Characteristics

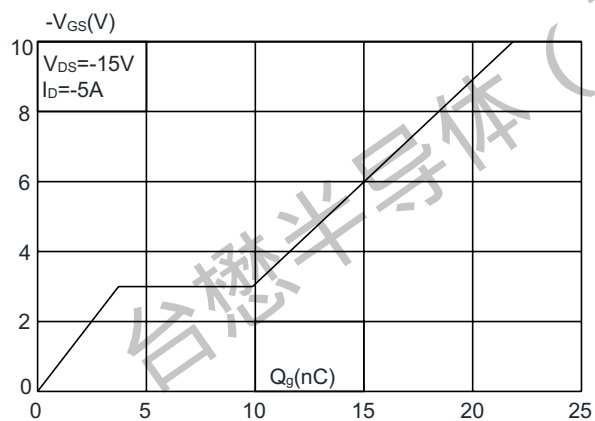
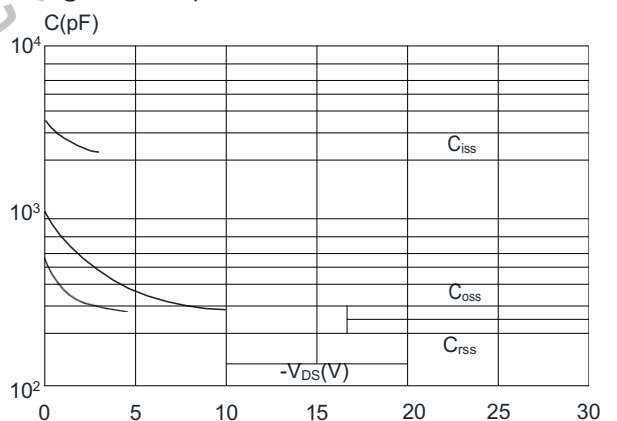


Figure 6: Capacitance Characteristics



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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

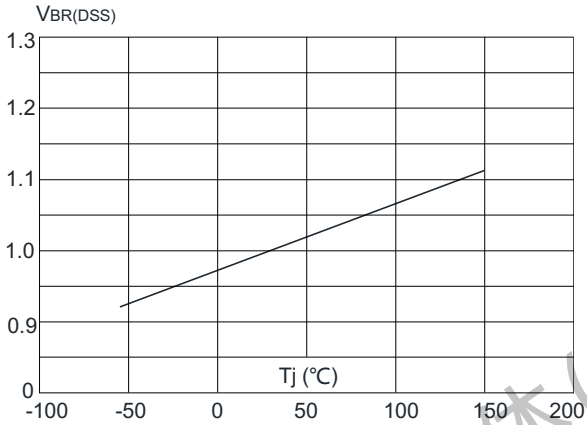


Figure 8: Normalized on Resistance vs. Junction Temperature

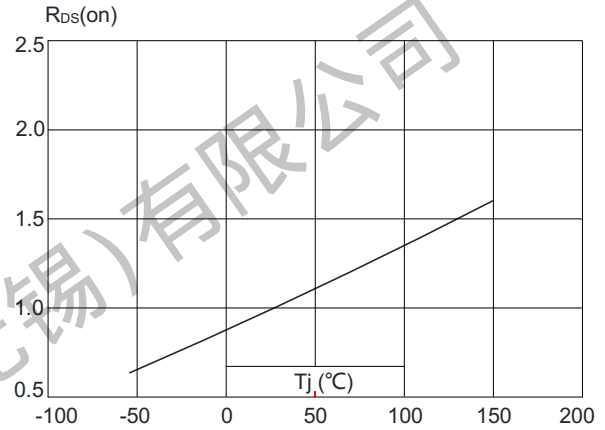


Figure 9: Maximum Safe Operating Area

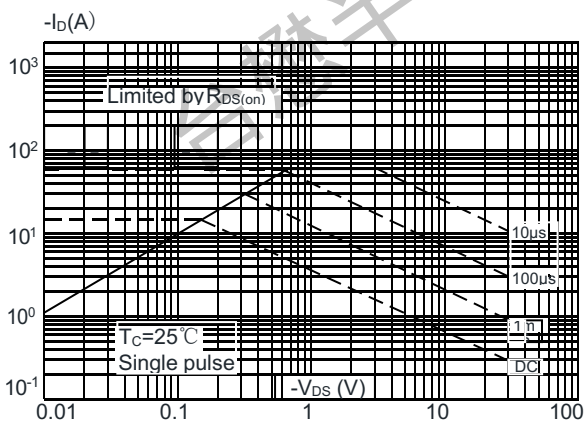


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

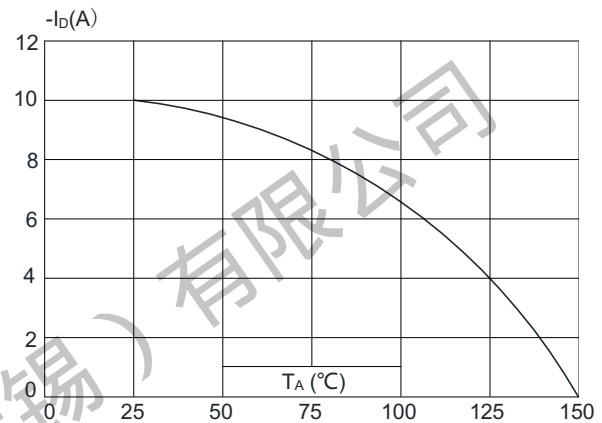
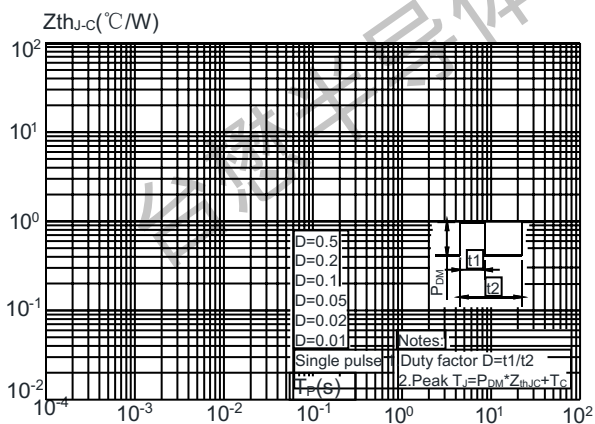


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

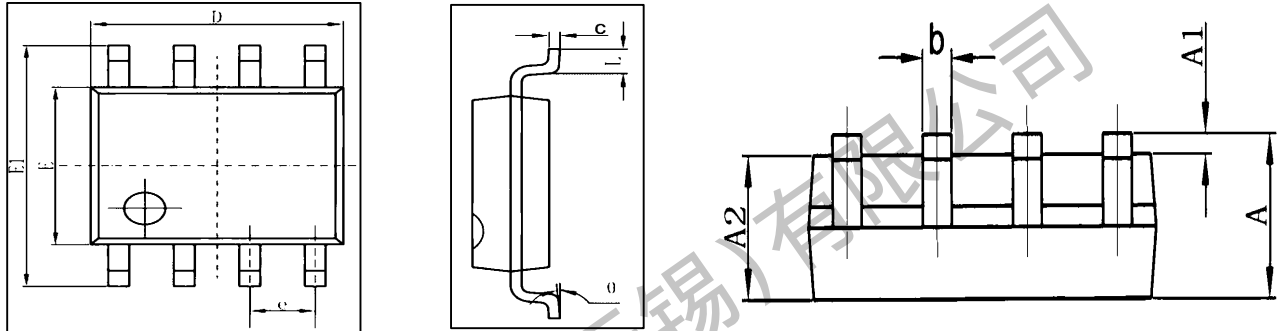




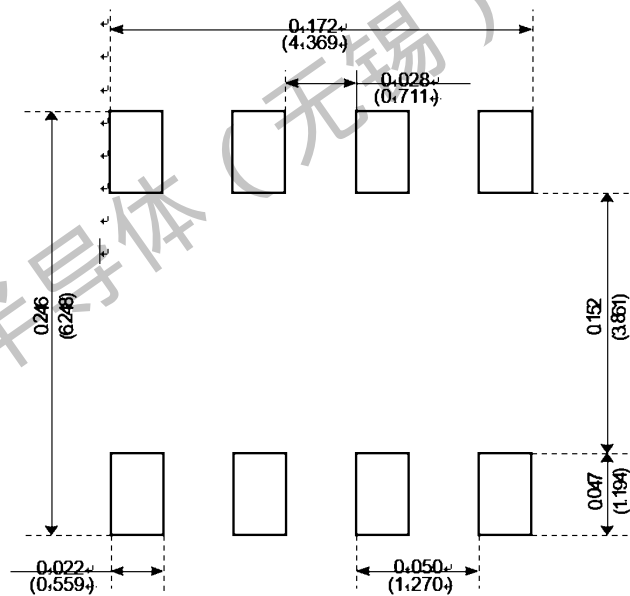
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Package Mechanical Data:SOP-8L



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min | Max | Min | Max |
| A | 1.350 | 1.750 | 0.053 | 0.069 |
| A1 | 0.100 | 0.250 | 0.004 | 0.010 |
| A2 | 1.350 | 1.550 | 0.053 | 0.061 |
| b | 0.330 | 0.510 | 0.013 | 0.020 |
| c | 0.170 | 0.250 | 0.006 | 0.010 |
| D | 4.700 | 5.100 | 0.185 | 0.200 |
| E | 3.800 | 4.000 | 0.150 | 0.157 |
| E1 | 5.800 | 6.200 | 0.228 | 0.244 |
| e | 1.270 (BSC) | | 0.050 (BSC) | |
| L | 0.400 | 1.270 | 0.016 | 0.050 |
| θ | 0° | 8° | 0° | 8° |

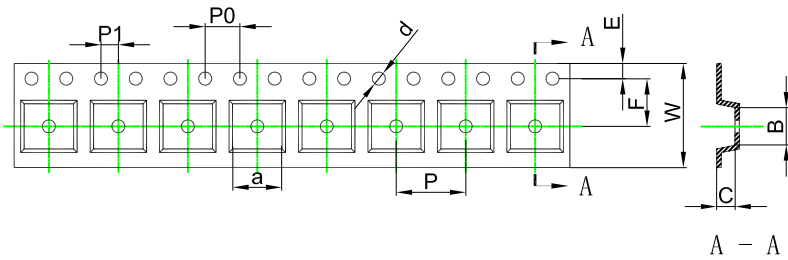


Recommended Minimum Pads

TM10V03S

P+P-Channel Enhancement Mode Mosfet

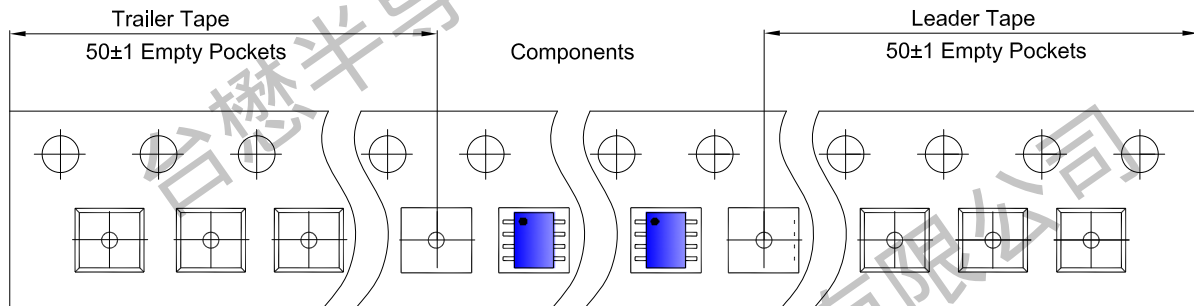
SOP-8L Embossed Carrier Tape



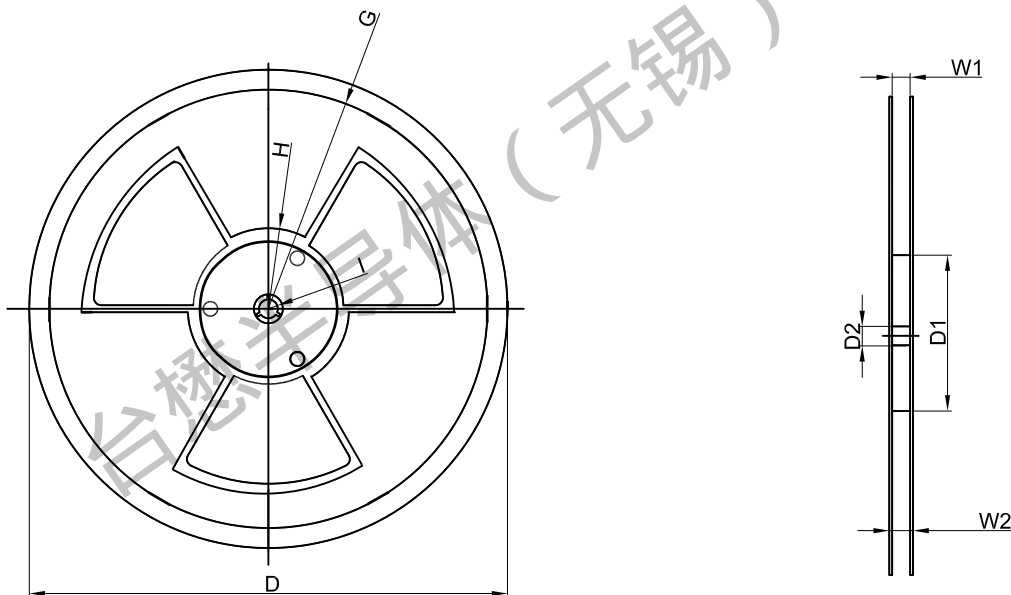
Packaging Description:
SOP-8L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13" or 33cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).
ALL DIM IN mm

| Dimensions are in millimeter | | | | | | | | | | |
|------------------------------|------|------|------|-------|------|------|------|------|------|-------|
| Pkg type | a | B | C | d | E | F | P0 | P | P1 | W |
| SOP-8L | 6.40 | 5.40 | 2.10 | Ø1.50 | 1.75 | 5.50 | 4.00 | 8.00 | 2.00 | 12.00 |

SOP-8L Tape Leader and Trailer



SOP-8L Reel



| Dimensions are in millimeter | | | | | | | | |
|------------------------------|---------|--------|-------|---------|--------|-------|-------|-------|
| Reel Option | D | D1 | D2 | G | H | I | W1 | W2 |
| 13" Dia | Ø330.00 | 100.00 | 13.00 | R135.00 | R55.00 | R6.50 | 12.00 | 14.00 |

| REEL | Reel Size | Box | Box Size(mm) | Carton | Carton Size(mm) | G.W.(kg) |
|-----------|-----------|-----------|--------------|------------|-----------------|----------|
| 3,000 pcs | 13 inch | 6,000 pcs | 370×355×52 | 48,000 pcs | 400×360×368 | |



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| 2023.07.21 | 23.07 | Original | |